

General Description

These N-channel MOSFET are produced using advanced Magnachip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

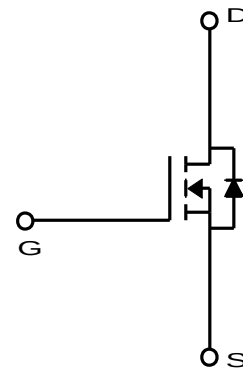
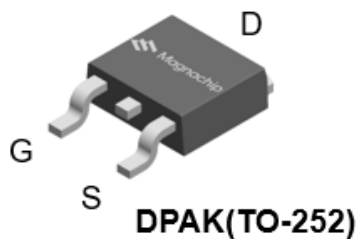
These devices are suitable device for SMPS, high Speed switching and general purpose applications.

Features

- $V_{DS} = 600V$
- $I_D = 1.9A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} \leq 4.5\Omega$ @ $V_{GS} = 10V$

Applications

- Power Supply
- PFC
- High Current, High Speed Switching



Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	$T_C=25^\circ C$	I_D	1.9	A
	$T_C=100^\circ C$		1.2	A
Pulsed Drain Current ⁽¹⁾		I_{DM}	7.6	A
Power Dissipation	$T_C=25^\circ C$	P_D	42	W
	Derate above 25 °C		0.34	W/°C
Repetitive Avalanche Energy ⁽¹⁾		E_{AR}	4.2	mJ
Peak Diode Recovery dv/dt ⁽³⁾		dv/dt	4.5	V/ns
Single Pulse Avalanche Energy ⁽⁴⁾		E_{AS}	115	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	°C

* Id limited by maximum junction temperature

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	110	°C/W
Thermal Resistance, Junction-to-Case ⁽¹⁾	$R_{\theta JC}$	2.98	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDD2N60RH	-55~150°C	D-PAK	Reel	Halogen Free

Electrical Characteristics (Ta =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu A, V_{GS} = 0V$	600	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	-	5.0	
Drain Cut-Off Current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$	-	-	1	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 0.95A$		3.6	4.5	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30V, I_D = 1.0A$	-	0.5	-	S
Dynamic Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 480V, I_D = 2.0A, V_{GS} = 10V^{(3)}$	-	6.7		nC
Gate-Source Charge	Q_{gs}		-	2.2		
Gate-Drain Charge	Q_{gd}		-	2.5		
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	-	275	360	pF
Reverse Transfer Capacitance	C_{rss}		-	1.4	2	
Output Capacitance	C_{oss}		-	32	40	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 300V, I_D = 2.0A, R_G = 25\Omega^{(3)}$	-	10.6		ns
Rise Time	t_r		-	29.6		
Turn-Off Delay Time	$t_{d(off)}$		-	40.4		
Fall Time	t_f		-	38.4		
Drain-Source Body Diode Characteristics						
Maximum Continuous Drain to Source Diode Forward Current	I_S		-	4.6	-	A
Source-Drain Diode Forward Voltage	V_{SD}	$I_S = 1.9A, V_{GS} = 0V$	-		1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 2.0A, di/dt = 100A/\mu s$	-	206		ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.76		μC

Note :

- Pulse width is based on $R_{\theta JC}$ & $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.
- Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ C$.
- $I_{SD} \leq 2.0A$, $di/dt \leq 200A/\mu s$, $V_{DD} = 50V$, $R_g = 25\Omega$, Starting $T_J = 25^\circ C$
- $L = 53mH$, $I_{AS} = 2.0A$, $V_{DD} = 50V$, $R_g = 25\Omega$, Starting $T_J = 25^\circ C$,

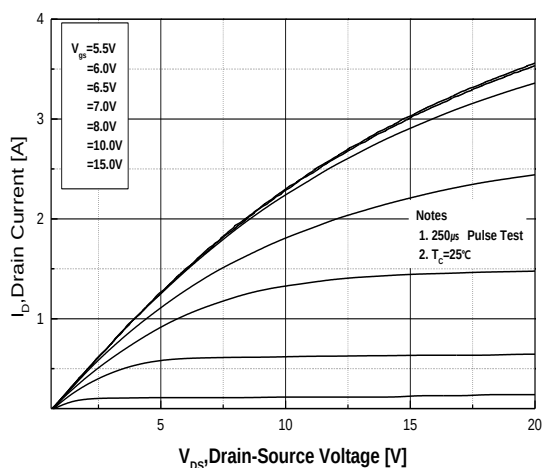


Fig.1 On-Region Characteristics

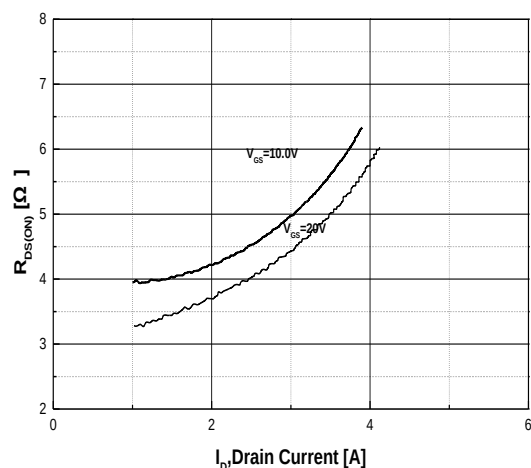


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

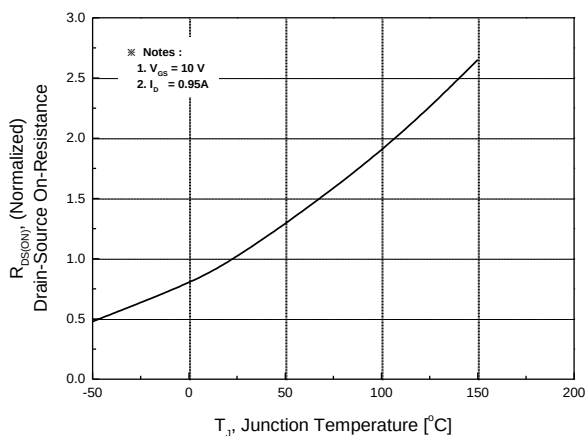


Fig.3 On-Resistance Variation with Temperature

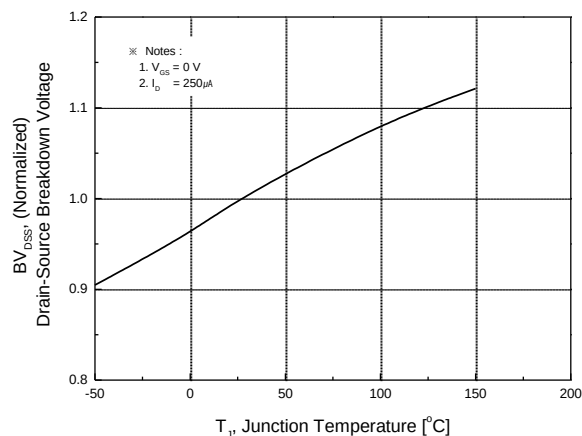


Fig.4 Breakdown Voltage Variation vs. Temperature

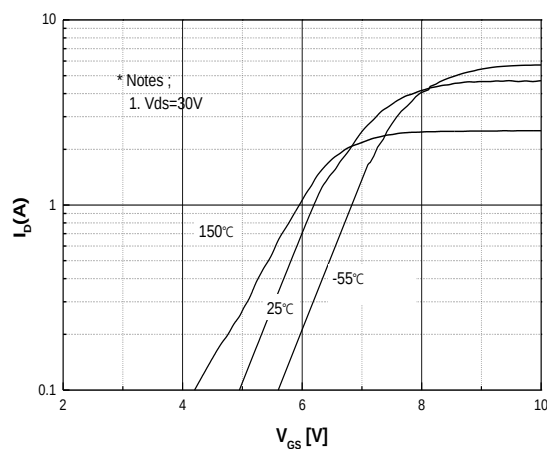


Fig.5 Transfer Characteristics

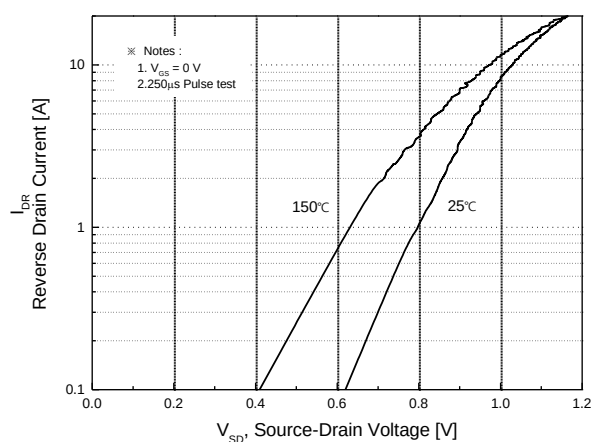
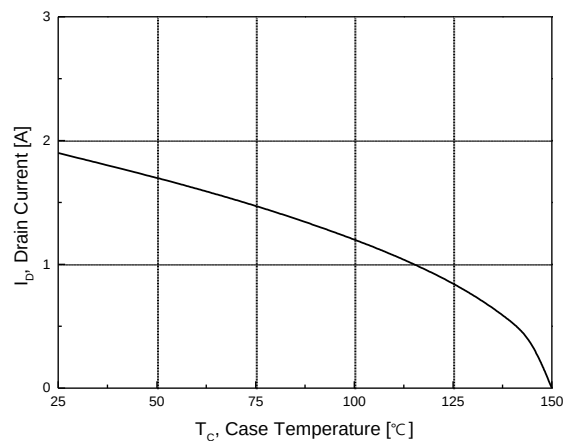
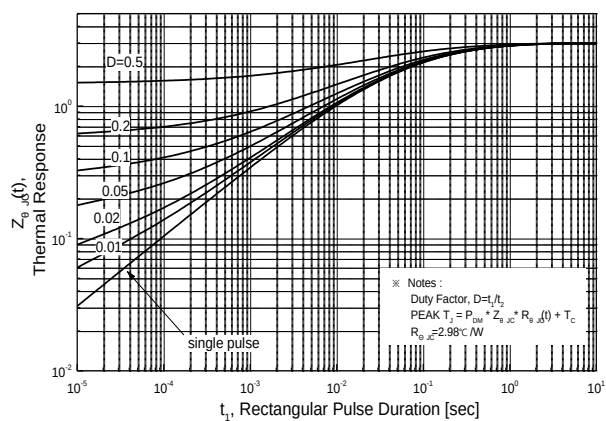
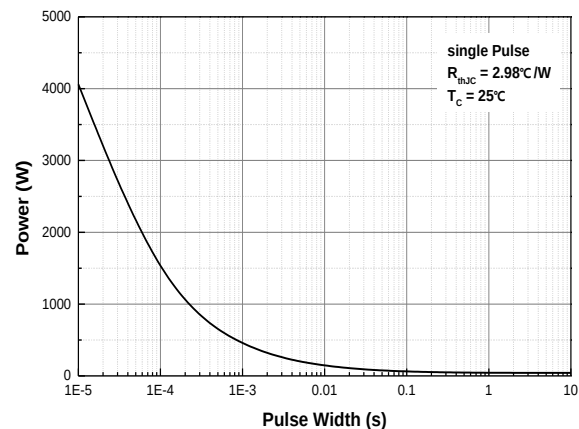
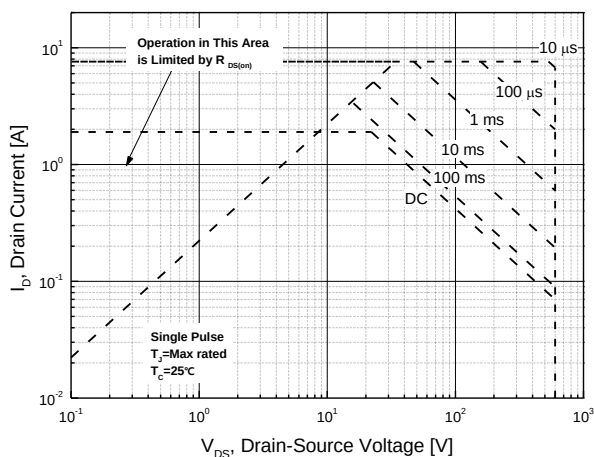
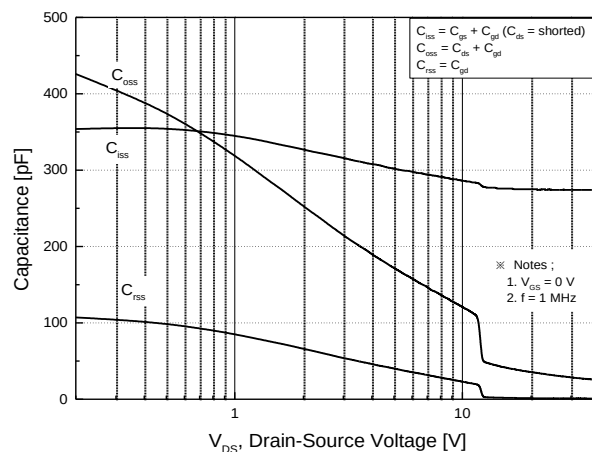
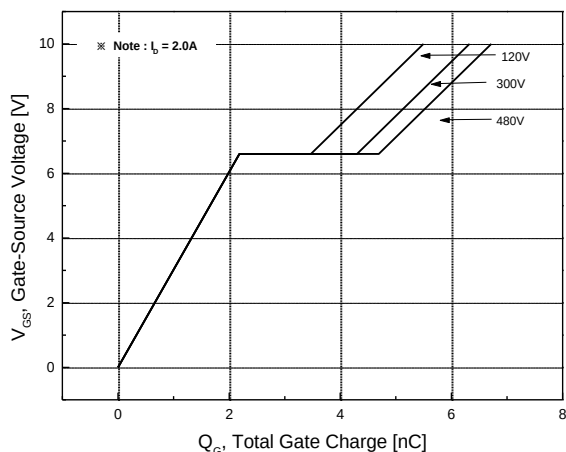


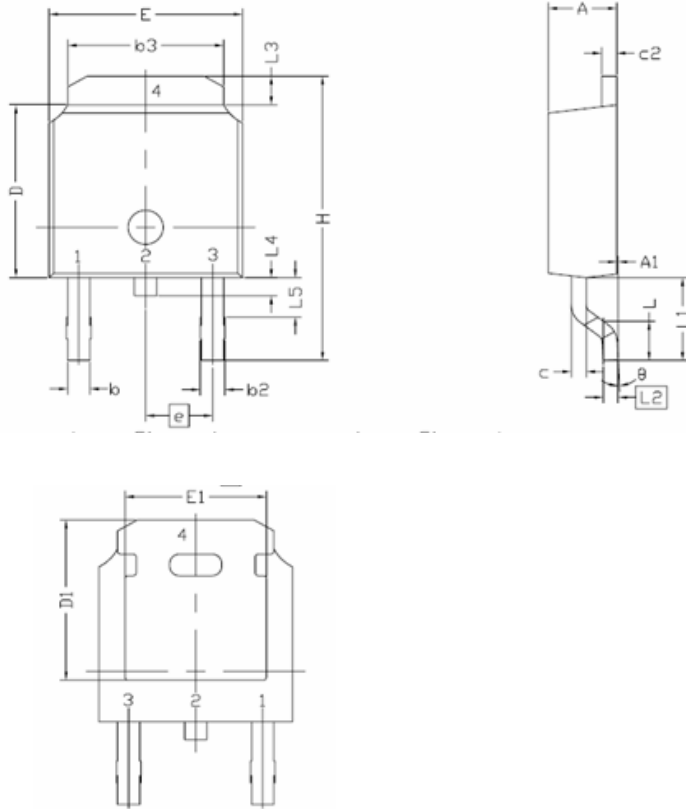
Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature



Physical Dimension

TO-252 (DPAK)

Dimensions are in millimeters, unless otherwise specified



Symbol	Min.	Nom.	Max.
E	6,35	-	6,73
L	1,40	1,52	1,78
L1	2,74 REF		
L2	0,508 BCS		
L3	0,89	-	1,27
L4	-	-	1,02
L5	1,14	-	1,52
D	5,97	6,10	6,22
H	9,40	-	10,41
b	0,64	-	0,89
b2	0,76	-	1,14
b3	4,95	-	5,46
e	2,286 BSC		
A	2,18	-	2,39
A1	-	-	0,13
c	0,46	-	0,61
c2	0,46	-	0,89
D1	5,21	-	-
E1	4,32	-	-
⌀	0,00	-	10,00

Worldwide Sales Support Locations

U.S.A

Sunnyvale Office

787 N. Mary Ave. Sunnyvale
CA 94085 U.S.A
Tel : 1-408-636-5200
Fax : 1-408-213-2450
E-Mail : usasales@magnachip.com

U.K

Knyvett House The Causeway,
Staines Middx, TW18 3BA, U.K.
Tel : +44 (0) 1784-895-000
Fax : +44 (0) 1784-895-115
E-Mail : uksales@magnachip.com

Japan

Osaka Office

3F, Shin-Osaka MT-2 Bldg 3-5-36
Miyahara Yodogawa-Ku
Osaka, 532-0003 Japan
Tel : 81-6-6394-9160
Fax : 81-6-6394-9150
E-Mail : osakasales@magnachip.com

Taiwan R.O.C

2F, No.61, Chowize Street, Nei Hu
Taipei, 114 Taiwan R.O.C
Tel : 886-2-2657-7898
Fax : 886-2-2657-8751
E-Mail : taiwansales@magnachip.com

China

Hong Kong Office

Suite 1024, Ocean Centre 5 Canton Road,
Tsim Sha Tsui Kowloon, Hong Kong
Tel : 852-2828-9700
Fax : 852-2802-8183
E-Mail : chinasales@magnachip.com

Shenzhen Office

Room 2003B, 20/F
International Chamber of Commerce Tower
Fuhua Road3 CBD, Futian District, China
Tel : 86-755-8831-5561
Fax : 86-755-8831-5565
E-Mail : chinasales@magnachip.com

Shanghai Office

Room E, 8/F, Liaoshen International Building 1068
Wuzhong Road, (C) 201103
Shanghai, China
Tel : 86-21-6405-1521
Fax : 86-21-6505-1523
E-Mail : chinasales@magnachip.com

Korea

891, Daechi-Dong, Kangnam-Gu
Seoul, 135-738 Korea
Tel : 82-2-6903-3451
Fax : 82-2-6903-3668 ~9
Email : koreasales@magnachip.com

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